

Mounding Instability and Incoherent Surface Kinetics

S.V. Ghaisas

Department of Electronic Science, University of Pune, Pune 411007, India
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Mounding instability in a conserved growth from vapor is analysed within the framework of adatom kinetics on the growing surface. The analysis shows that depending on the local structure on the surface, kinetics of adatoms may vary, leading to disjoint regions in the sense of a continuum description. This is manifested particularly under the conditions of instability. Mounds grow on these disjoint regions and their lateral growth is governed by the flux of adatoms hopping across the steps in the downward direction. A symptotically $\ln t$ dependence is expected in 1+1-dimensions. Simulation results confirm the prediction. Growth in 2+1-dimensions is also discussed.

Mounding instability was experimentally observed and proposed by Johnson et. al [1] during growth of GaAs on (001) GaAs substrate. Initially, activation difference (Schwoebel-Ehrlich (SE) barrier) [2] between adatoms hopping on the plane and the one crossing the step edge was considered responsible [3]. Later it was shown that edge diffusion can also lead to similar effect [4]. One of the issues related to growth of mounds has been the temporal dependence of mound growth. Based on various forms of continuum equations the lateral growth is expected to have a time dependence t^s where s takes values from 0.0 to 1/4 [5]. Similarly, the width of the interface is predicted to follow the power law t with varying from 1/3 onwards [5]. All these predictions are based on the assumption that the underlying conserved growth equation describing non equilibrium growth, is valid over the entire substrate. In the following we show that under the conditions of instability and low temperatures, this assumption fails. Consequently the growth of mounds is governed laterally by the adatom kinetics across the mound boundaries. We show this by developing growth equation over a stepped surface in 1+1 dimensions using kinetics of adatoms and steps. This helps establish the correspondence between kinetic processes and terms in the growth equation. We assume that only mechanism of relaxation is by diffusion of adatoms. This allows identification of process and corresponding term uniquely. These assumptions are expected to be valid at low temperature, where evaporation is negligible. Once the kinetic processes leading to various terms in growth equation are identified, presence or absence of such terms in various regions on the surface can be predicted. This allows us to classify different regions on the surface according to the growth equation followed there.

Consider growth on a one dimensional substrate. Fig.1 shows the stepped region under consideration. Growth proceeds through randomly falling adatoms on the surface that relax by diffusing on the stepped terraces. Adatoms with zero nearest neighbors (nn) are mobile while those with more than zero nn will have negligible mobility. Further, desorption and dissociation from

the steps is also negligible at low temperature. Under the conserved growth conditions it is possible to write formally the growth equation in the form $\partial_t h(x;t) = r - j(x;t) + F$, where, F is incident flux, $h(x;t)$ is height function and $j(x;t)$ is particle current. An uphill current on a tilted substrate indicates instability while downhill indicates stable Edward-Wilkinson (EW) [6] type growth [7]. Let l_d be the average length travelled by an adatom before getting attached to another adatom or step. The density of steps can be expressed as $\frac{j_n j}{1 + j_n j}$. Let P_A and P_B be the relative probabilities for hopping across the sites A and B in Fig. 1. By considering current due to the downward hops and that due to the in-plane hops separately, one can show that the resultant nonequilibrium current is given by [8]

$$j_s = \frac{\hat{n} j_n F (P_B - P_A)}{2(1 + j_n j)(l_d^{-1} + j_n j^{-1})} \quad (1)$$

Where \hat{n} denotes +ve x direction. Presence of l_d^{-1} in the denominator accounts for the nucleation effect on larger terraces. In this expression, local terrace width is $(l_d^{-1} + a^{-1} j_n j)^{-1}$. However due to the relative velocity between two adjacent terraces, the local terrace width changes. The velocity difference will be proportional to the $\frac{\partial j(x;t)}{\partial x}$. Including this dynamical effect, the expression for the current becomes,

$$j(x) = \frac{\hat{n} j_n F (P_B - P_A)}{2(1 + j_n j)(l_d^{-1} + j_n j^{-1})} - \frac{\hat{n} F}{4} \partial_x \left[\frac{j_n j}{(1 + j_n j)(l_d^{-1} + j_n j^{-1})} \right]^2 \quad (2)$$

Next, we argue that every downward hop introduces height-height correlation, hence will give rise to all the stabilizing terms in a growth equation. Under the tilt independent current conditions, the lowest of such terms is $K \frac{\partial^3 h}{\partial x^3}$. Thus the current on the stepped surface will be,

$$j(x) = \frac{\hat{n} j_n F (P_B - P_A)}{2(1 + j_n j)(l_d^{-1} + j_n j^{-1})}$$

$$\frac{\partial^2 h}{\partial x^2} \frac{\partial F}{\partial x} + \frac{j_x j_y}{(1 + j_x j_y) (l_d^{-1} + j_x j_y^{-1})} + \frac{\partial^3 h}{\partial x^3} \quad (3)$$

For small slopes, above current generates growth equation in the moving frame with average growth rate,

$$\frac{\partial h(x;t)}{\partial t} = \frac{F(P_B - P_A) l_d}{2} \frac{\partial^2 h}{\partial x^2} + \frac{F l_d^2}{4} \frac{\partial^2}{\partial x^2} \frac{\partial h}{\partial x} + k \frac{\partial^4 h}{\partial x^4} + \xi(x;t) \quad (4)$$

Where, $\xi(x;t)$ is the Gaussian noise in the deposition with the property, $\langle \xi(x^0;t^0) \xi(x;t) \rangle = \delta(x^0 - x) \delta(t^0 - t)$. For $P_A = P_B$, current is tilt free, corresponding equation has the Lai-Das Sarma - Villain [9,3] form.

Now consider a top terrace. By definition, only tilt independent terms will contribute. Also since steps are absent the only term that contributes is, $k \frac{\partial^3 h}{\partial x^3}$ due to the downward hops at the edges. For a base terrace, only in-plane hops are possible, hence none of the above terms contribute. This shows that these regions offer restricted kinetics, thereby changing the growth equation locally. If these regions are smaller than l_d , they will act only as the regions of discontinuity. Villain [10] encountered this difference in connection with simulations using Zeno equations. However so far it has been assumed that a given growth equation is valid over the complete substrate and such a distinction is irrelevant under coarsening. Based on above argument we propose that stepped, top and base terraces are distinct regions where different growth equation applies. Thus, in growth from vapor at low temperature, scalability breaks down. However, in simulations and experiments, kinetically rough surfaces are observed. This is possible provided steps develop in base and top regions at a rate comparable with the growth of correlation length defined by the equation over steps, shifting these regions. It may be noted that since downward hops allow addition of material to lower layers, average shifting of top or base region is possible only if downward hops are present. An infinite SE barrier leads to such an immobilization of top and bases [11]. This is the limiting example displaying the effect of three independent regions on growth. If average shift of top or base regions lags behind the correlation growth, mounding instability appears. The lateral growth of the mounds being decided by the lateral shift of base regions. It has been established that stability of the growth can be quantified in terms of tilt dependent current j_t . For $j_t > 0$ (uphill), unstable growth while for $j_t < 0$, stable growth is obtained, where j_t is measurable in a simulation by properly adjusting the boundary conditions [7]. Thus, for uphill current, base or top regions lag behind the correlations while for downhill it shifts at least as fast as correlations.

Consider unstable growth in 1+1 dimensions. Fig.2 shows the well developed mounds. Note the deep ridges

formed due to high step heights of the steps forming the ridges. The model used for this growth will be described later. It suffices to know that it's a growth with finite diffusion of adatoms and finite SE barrier. We estimate the growth rate by appealing to the diffusional kinetics of adatoms. The growth proceeds by expansion of a larger mound at the cost of smaller one [10]. Thus the ridge proceeds in one direction. A smaller mound generally poses a smaller angle with respect to the substrate. Thus, relatively longer terraces are present on this mound. The diffusional addition to the ridges is mainly from these terraces, resulting in to the shift of ridge in the direction of smaller mound. Thus, we assume that adatoms are added from the smaller mound, diffusively. The diffusional rate of displacement is $dl = D_s^{1/2} t^{1/2} dt$ on a plane surface in time dt . However, for a ridge to move laterally, it must be lifted at least up to first step height. For sharp ridges as in Fig.2, the step height of ridge may be taken to be w , the rms height fluctuation (width). Hence, the displacement for a ridge will be $dl_r = p D_s^{1/2} t^{1/2} a w^{-1}$. Where, p is relative fraction of adatoms crossing the step edge and a is lattice constant. For $w \propto t^{1/2}$, the growth of mounds is proportional to $\ln t$.

We verify the $\ln t$ dependence for a 1+1 dimensional model that mimics the growth at low temperature. In this model, on a one dimensional substrate, adatoms are rained randomly. An atom with one or more nn is incorporated in the crystal. An adatom with zero nn is allowed to hop n number of times at the most. If it acquires a nn, then no further hops are allowed. If number of hops are exhausted, it is incorporated at the final site after n hops. A parameter p is introduced, such that for $p > 0.5$ hopping across a step in the downward direction is difficult. $p = 1$ is the case of infinite SE barrier. We have measured $\langle h_i h_j \rangle$ correlations for various values of p and used the first zero crossing as the measure of the size of the mound. In Fig. 3, plot of mound size V vs. time on a semi-log scale clearly shows that for $p > 0.5$ i.e. for positive SE barrier, the mounds growth is $\ln t$. Also shown is the case for $p = 0.5$. We plot length corresponding to the first maximum in height-height correlations for this case. The curve on semi-log plot is exponential showing a power law dependence. Correlation length $\propto t^{1/4}$ in this case. In fact it can be shown [8] that corresponding equation describes Das Sarma - Tamboorenea (DT) [12] model to which the tilt independent growth equation reduces for large slopes. We find that for $p < 0.5$, asymptotically, EW growth is recovered. Thus, the base and top regions move at least in phase with the rough surface. In the present model dissociation from steps is not included so that the detailed balance is not followed. If this is included, and the current is still uphill then $\ln t$ dependence continues for growth in 1+1-dimension.

Above arguments are true in any dimension. In 2+1-

dimensions, mound formation is observed experimentally as well as in simulations [1,13]. Various predictions are referred in the introduction above regarding the time evolution of the mounds. The $\ln t$ dependence in $1+1$ -dimensions is the upper limit for lateral development of the mounds in $2+1$ -dimensions. This is so because, a given mound is surrounded by four or more mounds. Probability that such a mound happens to be the smallest amongst the surrounding ones including itself is very small. A given mound may be reduced in one direction, but it may increase in other direction owing to a smaller mound there. Thus, instead of consumption, shift of mounds is more likely on a two dimensional substrate. In order to find the time dependence of mound growth in $2+1$ -dimensions, we have used same model described above, except that the rules apply in two directions on a square lattice. In addition, we have included edge diffusion with no edge barriers. It is observed that edge diffusion succeeds to induce uphill current so that even if the diffusion of single adatoms is unbiased, mound formation is observed. In the absence of edge diffusion but with unbiased single adatom diffusion, EW type growth is obtained [14]. Noise reduction technique [15] is employed with reduction factor of 5. The growth of mound size is monitored in the same way as for the $1+1$ -dimensions, using zero crossing for the correlations $\langle h_i h_j \rangle$. Fig.4 shows the plot of mound size as a function of time on semi-log plot. Clearly, after an initial growth like $\ln t$, the curve tends to saturation, confirming the slower growth rate. By varying parameter p , a condition close to tilt independent current is obtained. The growth in that case follows, $t^{1/4}$ power law. From the arguments leading to Eq.4, in $2+1$ -dimensions, we find that asymmetric term will be ineffective if step edge tension is lower so that steps morphology is wavy or fingered. This is so because, the terrace size can be reduced by step movements in the orthogonal directions as well. Thus only $r^4 h$ term contributes, leading to $\beta = 1/4$ and $z = 4$ in $2+1$ -dimensions. Clearly, this observation suggests that in experimental growth, if SE barrier is very small (but nonzero), at low temperature growth rate of mounds can be $t^{1/4}$ in the transient region. If the edge tension is high so that steps are straight and less wavy, asymmetric term can contribute with β and z , characteristics of a Lai-Das Samma like equation [9] in the transition region.

In conclusion, we have shown that growth from vapor on surface proceeds via in principle a heterogeneous dynamics. The stepped, base and top regions on the surface allow different growth dynamics. As a result the spatial scalability breaks down. The effect is distinctly observable for unstable growth leading to mound formation. The kinetics across the mounds suggest a $\ln t$ dependence in $1+1$ -dimensions which is verifiable in a suitable model. A slower growth is predicted in $2+1$ -dimensions which is also observed in a model simulation.

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- [1] M.D. Johnson, C.Ommé, A.W. Hunt, D.Gra, J. Sudipno, L.M. Sander and B.G. Orr, Phys. Rev. Lett. 72, 116 (1994)
 - [2] G. Ehrlich and F. Hudda, J. Chem. Phys. 44, 1039 (1966); R.L. Schwoebel, J. Appl. Phys. 40, 614 (1969).
 - [3] J. Villain, J. Phys. I 1, 19 (1991).
 - [4] O. Pierre-Louis, M.R. D'Orosogna and T.L. Einstein, Phys. Rev. Lett. 82, 3661 (1999); M.V. Ramamurty and B.H. Cooper, Phys. Rev. Lett. 83, 352 (1999).
 - [5] Golubovic L., Phys. Rev. Lett. 78, 90 (1997); M. Siegert and M. Plischke, Phys. Rev. Lett. 73, 1517 (1994).
 - [6] S.F. Edwards and D.R. Wilkinson, Proc. R. Soc. London A 381, 17 (1982).
 - [7] J. Krug, M. Plischke and M. Siegert, Phys. Rev. Lett., 70, 3271 (1993).
 - [8] Preprint No. cond-mat/0202210 (2002).
 - [9] Z.W. Lai and S.Das Samra, Phys. Rev. Lett. 66, 2348 (1991).
 - [10] P. Polity and J. Villain, Phys. Rev. B 54, 5114 (1996).
 - [11] Cohen P.I., Petrich G.S., Pukite P.R., Whaley G.J., and Arrott A.S., Surf. Sci., 216, 222 (1989).
 - [12] S.Das Samra and P. Tamborenea, Phys. Rev. Lett. 66, 325 (1991).
 - [13] J. Krug, Adv. Phys. 46, 141 (1997).
 - [14] P. Punyindu, Z. Toroczka and S.Das Samra, Surf. Sci. Lett. 457, L369 (2000). P. Punyindu and S.Das Samra, Phys. Rev. E 57, R4863 (1998).
 - [15] Kertesz J., Wolf D.E., J. Phys. A 21, 747 (1988); D.E. Wolf and Kertesz J., Europhys. Lett. 4, 651 (1987).

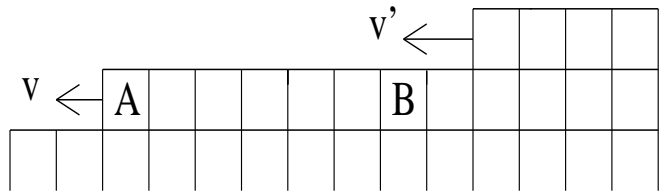


FIG. 1. A typical step structure formed during growth along positive slope. v and v^0 are velocities of the steps.

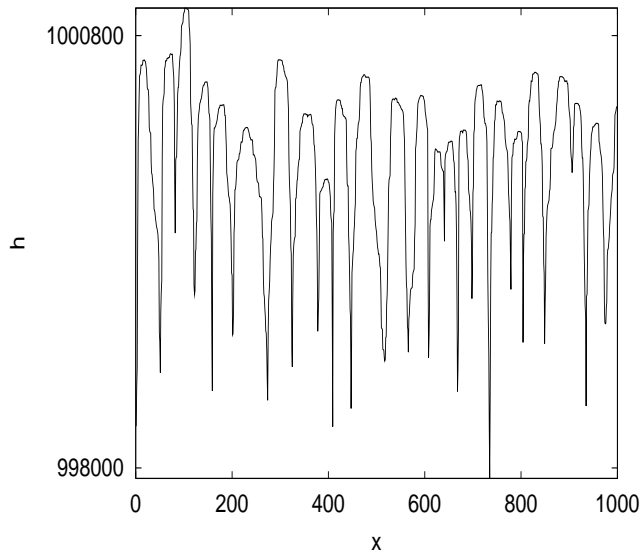


FIG .2. Morphology of the surface in 1+1-dimensions for an unstable growth after 10^6 layers. Parameter p is 0.6.

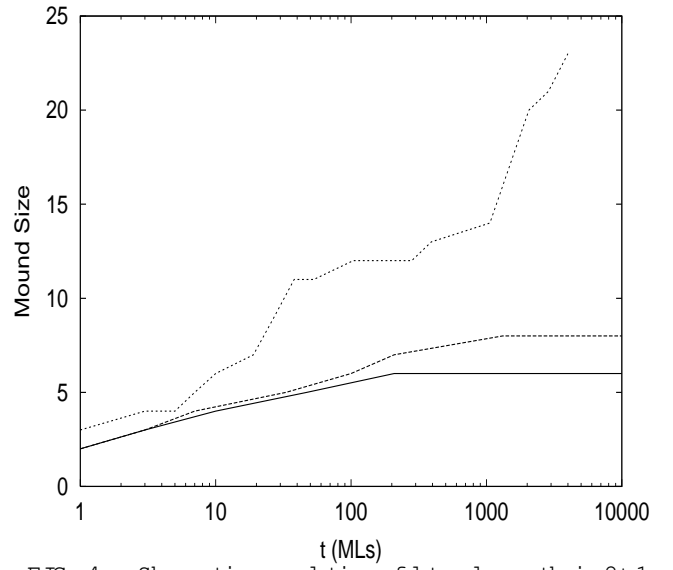


FIG .4. Shows time evolution of lateral growth in 2+1-dimensions. The values of parameter p are 0.35, 0.6, and 0.7 respectively for the curves from top to bottom in the figure. The substrate size is 300 X 300 for the simulation.

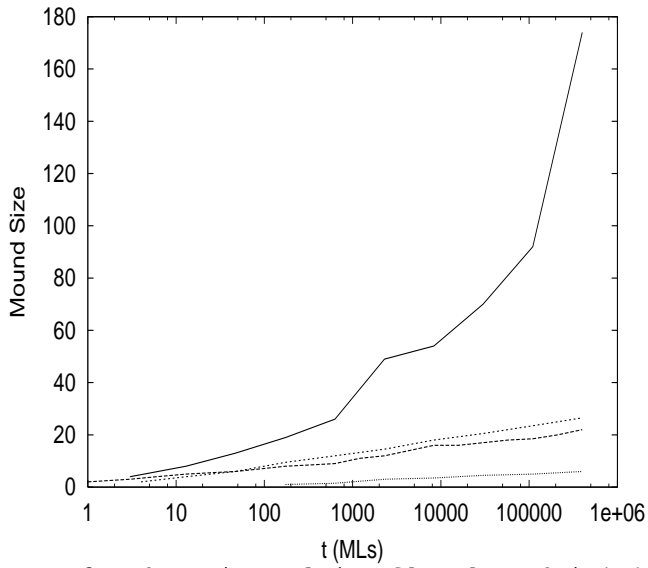


FIG .3. Shows time evolution of lateral growth in 1+1-dimensions. The values of parameter p are 0.5, 0.6, 0.7 and 0.8 respectively for the curves from top to bottom in the figure. The substrate size is $L = 10000$.